

SOT-523 Plastic-Encapsulate MOSFETS

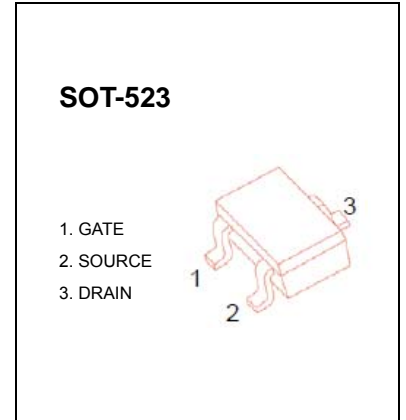
CJ1012 N-Channel Power MOSFET

General Description

This Single N-Channel MOSFET has been designed using advanced Power Trench process to optimize the $R_{DS(ON)}$.

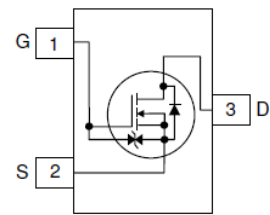
FEATURE

- High-Side Switching
- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- ESD protected up to 2KV



APPLICATIONS

- Drivers:Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagere



Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Units
Drain-Source voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Drain Current-Continuous	$I_{D(DC)}$	500	mA
Drain Current -Pulsed(note1)	$I_{DM(pulse)}$	1000	
Power Dissipation (note 2 , $T_a=25^{\circ}C$)	P_D	150	mW
Maximum Power Dissipation (note 3 , $T_c=25^{\circ}C$)		275	
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^{\circ}C/W$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	455	
Storage Temperature	T_j	150	$^{\circ}C$
Junction Temperature	T_{stg}	-55 ~+150	

Electrical characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
On/Off States						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.45		1.2	
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 4.5V$			± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16V, V_{GS} = 0V$			100	nA
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 600mA$			700	m Ω
		$V_{GS} = 2.5V, I_D = 500mA$			850	
Forward Transconductance	g_{FS}	$V_{DS} = 10V, I_D = 400mA$		1		S
Dynamic Characteristics						
Input Capacitance (note 4)	C_{iss}	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$		100		pF
Output Capacitance (note 4)	C_{oss}			16		
Reverse Transfer Capacitance (note 4)	C_{rss}			12		
Total Gate Charge	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V,$ $I_D = 250mA$		750		nC
Gate-Source Charge	Q_{gs}			75		
Gate-Drain Charge	Q_{gd}			225		
Switching Times (note 4)						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10V,$ $R_L = 47\Omega, I_D = 200mA,$ $V_{GS} = 4.5V, R_G = 10\Omega$		5		nS
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			25		
Fall Time	t_f			11		
Drain-Source Diode Characteristics						
Drain-Source Diode Forward Voltage (note 5)	V_{SD}	$I_S = 0.15A, V_{GS} = 0V$			1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at $T_a=25^\circ\text{C}$.
3. This test is performed with infinite heat sink at $T_c=25^\circ\text{C}$.
4. These parameters have no way to verify.
5. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$.

